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# N-Channel 20 V (D-S) 175 °C MOSFET

#### **DESCRIPTION**

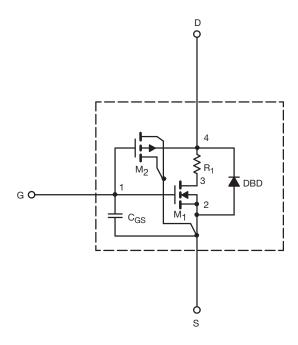
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- · Model the Gate Charge

#### SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



# SPICE Device Model SUD50N02-09P

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.7	-	V
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	438	-	Α
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	0.0078	0.0080	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	0.01	-	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A	0.0136	0.0135	
Diode Forward Voltagea	$V_{SD}$	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0 V	0.91	1.1	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	1212	1300	pF
Output Capacitance	C <sub>oss</sub>		470	470	
Reverse Transfer Capacitance	C <sub>rss</sub>		237	275	
Total Gate Charge <sup>c</sup>	Qg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A	10.6	10.5	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		4.2	4.2	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		4	4	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 10 \text{ V}, R_L = 0.2 \Omega$ $I_D = 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ $I_F = 50 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$	9	8	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		9	10	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		32	25	
Fall Time <sup>c</sup>	t <sub>f</sub>		10	12	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		31	35	

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

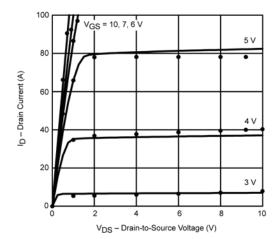
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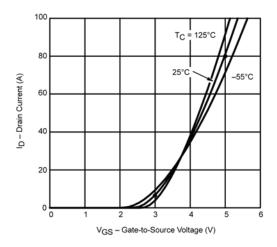
c. Independent of operating temperature.

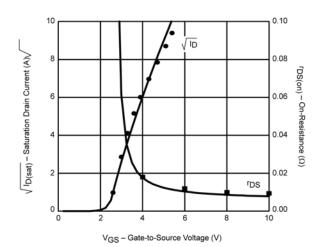
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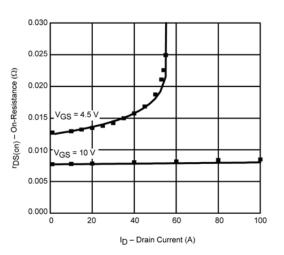
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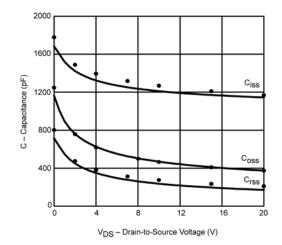
### COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)

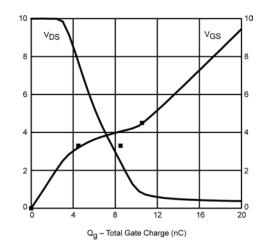












#### Note

• Dots and squares represent measured data.



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